Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	788672	(mount$4 attach$4 affix$4 fix$4) near2 (ic die chip dice capacitor transistor resistor diode part component inductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:21
L2	2110994	resin epoxy encapsulat$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:21
L3	2200	(pecvd or plasma adj enhanc$4) near2 (oxide or oxidat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:23
L4	0	1 same 3 and 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:23
L5	37	1 and 3 and 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:33
L6	31	5 and (@ad < "20021204")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 15:29
L7	7416	(plasma pecvd) near2 (clean$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:32
L8	2	1 and 3 and 2 and 7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:35
L9	2840	plasma near2 (ash$4) near8 (oxygen "o.sub.2" o2 ozone oxidiz$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:34
L10	1180	plasma near2 (clean$4) near8 (oxygen "o.sub.2" o2 ozone oxidiz$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:34

L11	598	peox pe adj ox peoxide pe adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:35
L12	2	1 and 3 and 2 and 10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:35
L13	139	1 and 2 and 10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:36
L14	6	1 same 10 and 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:38
L15	7	1 same 10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:38
L16	1	15 not 14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:38
L17	930	plasma near2 (clean$4 treat$8 irradat$6) near4 (contaminat$6 particle matter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 15:12
L18	7386	plasma near2 (clean$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 15:51
L19	6	1 same 17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 15:29
L20	163	1 same 18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 15:29

L21	40	1 adj8 18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 15:51
L22	30	21 and (@ad < "20021204")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 15:56
L23	422623	plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 15:51
L24	176	1 adj4 23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 15:55
L25	8	1 adj4 (after post next then subsequent$4) adj4 23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 15:56
L26	6	25 and (@ad < "20021204")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 16:17
L27	2	"6083775".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 16:17
L28	2	27 and (contamin$6 particl$4 organic inorganic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 16:21
L29	2	"5675177".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 16:21
L30	1	29 and (cu copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 16:28

L31	1	29 and (cu copper oxide oxid$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 16:31
L32	0	29 and (inert argon neon helium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 16:32
L33	0	27 and (inert argon neon helium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 16:45
L34	33	(plasma same inert same argon same neon same helium).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 16:46
L35	2291	((438/124) or (438/770) or (438/665) or (438/617)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 17:00
S95	2734	((438/1) or (438/2) or (438/3) or (438/4) or (257/5) or (257/6) or (257/7) or (257/8)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 16:58
S96	475200	(conduct$4 cu copper al aluminum zn zinc pt platinum pd palladium) near2 (foil layer metallization)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:25
S97	7378	plasma near2 (clean$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 15:12
S98	630123	(groove trench channel$4) near2 (etch$4 form$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:11
S99	2109472	resin epoxy encapsulat$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:21

S100	787886	(mount$4 attach$4 affix$4 fix$4) near2 (ic die chip dice capacitor transistor resistor diode part component inductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:21
S101	61	S100 same S97 same S99	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:49
S102	46	S101 and (@ad < "20021204")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:24
S103	29	S96 and S100 same S97 same S99	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:18
S104	20	S103 and (@ad < "20021204")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:50
S105	98540	(conduct$4 cu copper al aluminum zn zinc pt platinum pd palladium) near2 (foil)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:42
S106	22025	(thin$6 backgrind$4 grind$4 cmp planariz$4) near4 (foil)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:59
S107	2889	S100 same S105	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:45
S108	374	S107 and S106	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:45
S109	2	S108 and S97	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:45

S110	419730	(thin$6 backgrind$4 grind$4 cmp planariz$4) near4 (foil layer metallization)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:53
S111	47	S100 same S110 and S97	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:53
S112	45	S111 and (@ad < "20021204")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:46
S113	36628	(thinning thining backgrind$4 grind$4 cmp planariz$4) near4 (foil layer metallization)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:59
S114	2	S100 same S113 and S97	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:53
S115	2765	S106 and S100	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:59
S116	2179	S113 and S100	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 18:59
S117	393	(thinning thining backgrind$4 grind$4 cmp planariz$4) near4 (foil)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:00
S118	1	S117 and S100 and S97	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:43
S119	74	S113 and S100 and S97	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:03

S12 0	336604	(conduct$4 cu copper) near2 (foil layer metallization)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:28
S12 1	929	plasma near2 (clean$4 treat$8 irradat$6) near4 (contaminat$6 particle matter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 15:12
S12 2	0	S100 same S120 same S121 and S99	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:33
S12 3	4	S100 and S120 and S121 and S99	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:33
S12 4	6438	plasma near2 (clean$4 treat$8 irradat$6 cycl$6) near8 (oxygen "o. sub.2" o2 ozone)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:41
S12 5	69	plasma near2 (clean$4 treat$8 irradat$6 cycl$6) near4 (contaminat$6 particle matter) near8 (oxygen "o. sub.2" o2 ozone)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:43
S12 6	77	plasma near2 (clean$4 treat$8 irradat$6 cycl$6) near4 (contaminat$6 particle matter) near8 (oxygen "o. sub.2" o2 ozone oxidiz$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:45
S12 8	0	S126 and S100 and S99	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:46
S12 9	3	S126 and S100	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:44
S13 0	1178	plasma near2 (clean$4) near8 (oxygen "o.sub.2" o2 ozone oxidiz$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:34

S13 1	139	S130 and S100 and S99	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:56
S13 2	116	S131 and (@ad < "20021204")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:56
S13 3	6	S130 same S100 and S99	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 20:01
S13 4	5	S133 and (@ad < "20021204")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 19:56
S13 5	2837	plasma near2 (ash$4) near8 (oxygen "o.sub.2" o2 ozone oxidiz$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/30 14:34
S13 6	1	S135 same S100 and S99	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 20:02
S13 7	4	S135 same S100	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/29 20:02